Silicon N-Channel MOS FET

HITACHI

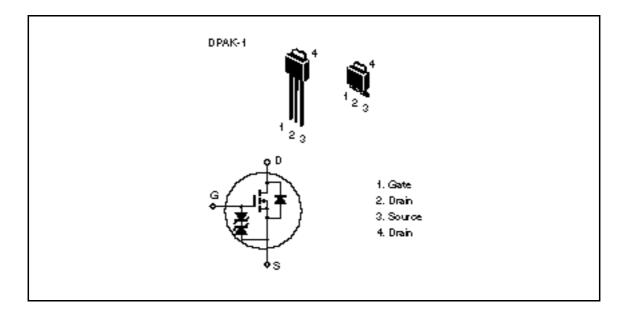
Application

High speed power switching

Features

- · Low on-resistance
- High speed switching
- Low drive current
- · No secondary breakdown
- Suitable for switching regulator and DC-DC converter

Outline





Absolute Maximum Ratings ($Ta = 25^{\circ}C$)

Item	Symbol Ratings		Unit	
Drain to source voltage	V _{DSS}	200	V	
Gate to source voltage	V_{GSS}	±20	V	
Drain current	I _D	3	А	
Drain peak current	l _{D(pulse)} *1	12	А	
Body to drain diode reverse drain current	I _{DR}	3	А	
Channel dissipation	Pch*2	20	W	
Channel temperature	Tch	150	°C	
Storage temperature	Tstg	-55 to +150	°C	

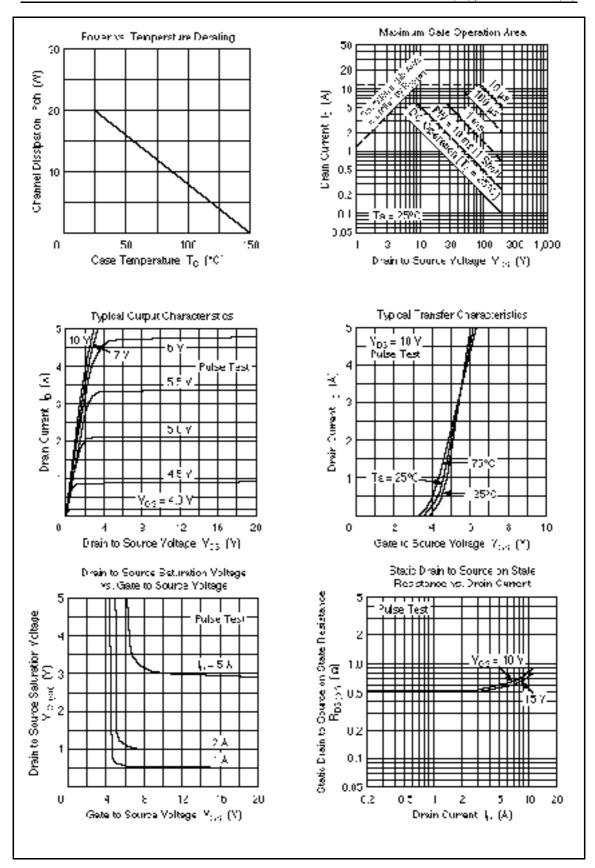
Notes: 1. PW 10 µs, duty cycle 1%

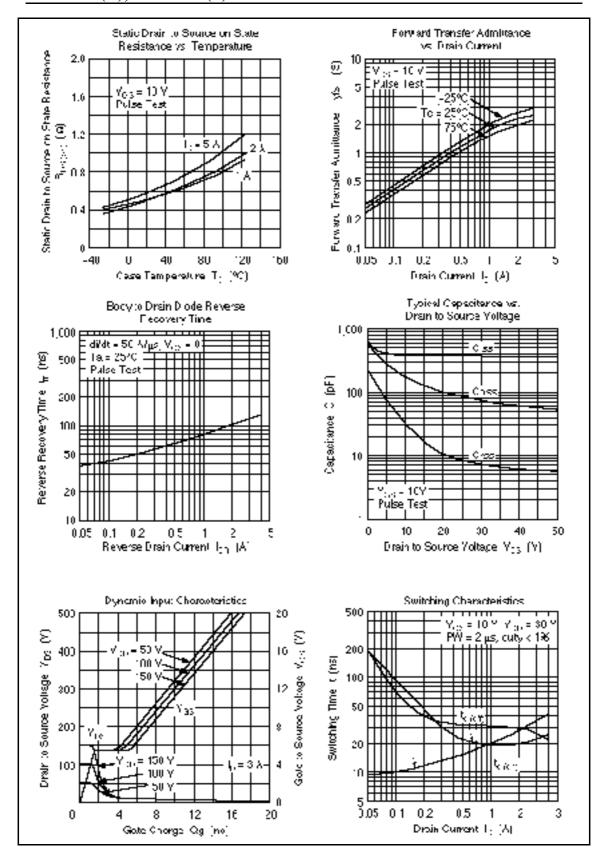
2. Value at $T_c = 25$ °C

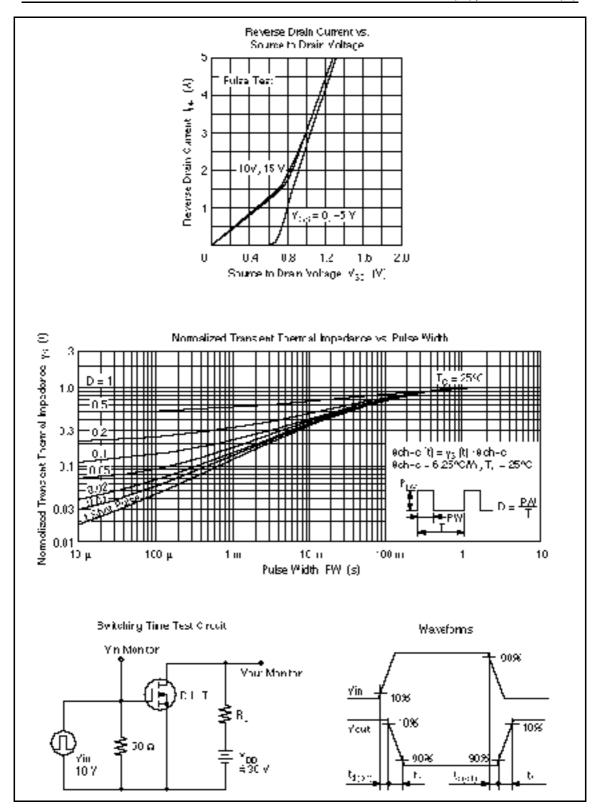
Electrical Characteristics ($Ta = 25^{\circ}C$)

Item	Symbol	Min	Тур	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	200	_	_	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	±20	_	_	V	$I_G = \pm 100 \ \mu A, \ V_{DS} = 0$
Gate to source leak current	I _{GSS}	_	_	±10	μΑ	$V_{GS} = \pm 16 \text{ V}, V_{DS} = 0$
Zero gate voltage drain current	I _{DSS}	_	_	100	μΑ	$V_{DS} = 160 \text{ V}, V_{GS} = 0$
Gate to source cutoff voltage	$V_{\rm GS(off)}$	2.0	_	4.0	V	$I_{\rm D} = 1 \text{ mA}, V_{\rm DS} = 10 \text{ V}$
Static drain to source on state resistance	$R_{\mathrm{DS(on)}}$	_	0.5	0.8		$I_D = 2 \text{ A}, V_{GS} = 10 \text{ V}^{*1}$
Forward transfer admittance	yfs	1.5	2.3	_	S	$I_D = 2 \text{ A}, V_{DS} = 10 \text{ V}^{*1}$
Input capacitance	Ciss	_	380	_	pF	$V_{DS} = 10 \text{ V}, V_{GS} = 0,$
Output capacitance	Coss	_	150	_	pF	
Reverse transfer capacitance	Crss	_	35	_	pF	_
Turn-on delay time	t _{d(on)}	_	10	_	ns	$I_D = 2 A, V_{GS} = 10 V,$
Rise time	t _r	_	27	_	ns	$R_L = 15$
Turn-off delay time	t _{d(off)}	_	30	_	ns	_
Fall time	t _f	_	20	_	ns	_
Body to drain diode forward voltage	V_{DF}	_	1.0	_	V	$I_F = 3 \text{ A}, V_{GS} = 0$
Body to drain diode reverse recovery time	t _{rr}	_	120	_	ns	$I_F = 3 \text{ A}, V_{GS} = 0,$ $di_F/dt = 50 \text{ A}/\mu\text{s}$

Note: 1. Pulse test







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